Anisotropic in-plane thermal conductivity observed in multilayer silicene

The thermal transportation properties of recently synthesized quasi-1D bulk is explored from first principle. The thermal conductivity of this system is found rather low because of the phonon localization caused by the low-dimension nature and large anharmonic scattering of phonons. Detailed analysis of lattice dynamic calculation is applied to explain the origin of the anharmonic effects. The Seebeck coefficients and electric conductance are calculated from first principle and then ZT value is given. We found is actually potential for the application of thermoelectric. This research could be a guidance for further exploring of advanced low thermal conductivity materials.

Keywords: Thermal conductivity, quasi-1D,, thermoelectric, phonons

I.INTRODUCTION

With the development of the existing silicon based circuit industry, the requirements of its integration and miniaturization make a lot of research work focusing on the application of the new two-dimensional materials. The theory and experiments in the last 10 years show that some new two-dimensional materials have many novel and excellent physical properties due to their structure and size. For example, the single atom layer MoS2 has a suitable band gap which makes its field effect transistor switching ratio as large as . Black phosphorus (BP) with thicknesses of several atomic layer have extremely high electron / hole mobility (1000) and leakage current modulation rates ( times of graphene) and the field effect transistor of it has great potential in the application of nano electronic devices. Due to the high thermal conductivity and electron mobility of graphene, it has great potential applications in the field of nano circuits. However, materials prepared in the practical application is often multilayer structure to a few nanometers. Previous studies have focused on the weak Van der Waals interaction (vdW), and there is no surface reconstruction. There have been lots of studies on the electronic and thermal transport properties for this kind of typical layered structure and hetero structures, such as graphene, MoS2, black phosphorus two-dimensional layered structure. The existing preparation technology such as mechanical stripping, molecular beam epitaxy has difficult to produce nano layered structure for the material with strong interaction between layers, and the research of this kind of super thin nano materials has been very scarce. Recently, it has been found that monolayer and multilayer silicon material can be grown on some metal substrates by molecular beam epitaxy. The progress of these experiments ignited the upsurge the two dimensional nanomaterials with strong interaction between layers. In contrast to vdW, the two layer nano materials, which are represented by multi-layer silicon, exhibit special surface reconstructions which are different from the bulk surface and its physical and chemical properties are also very unique, indicating that there is new physics in this kind of ultra-thin nano materials.

Silicon nano is currently the only one system, from its monolayer to multilayer, and then to the bulk structure, that have been prepared by experiment. And it has rich and typical structure in the dimension of zero dimension, one dimension and three dimensions, which have laid a very good foundation for the study of two-dimensional scale multilayer silicon. The study of multilayer silicon is also helpful to understand the physical evolution of matter from low dimension to high dimension. In addition, the preparation process of silicon nano materials is mature and the raw materials are rich, and It has a broad application prospect in the fields of micro nano electronics, energy, information and other important fields in the future.

At present, research of thermal transport properties based on the silicon nano structure mainly includes silicon nanowires, silicon graphene substrate support, silicon thin film and bulk structure. Due to the quantum size effect in the thickness direction and surface reconstruction effect, silicon multilayer structure is expected to have lower thermal conductivity than the bulk and is more suitable for thermoelectric applications. However, the study on the properties of multilayer silicon thermal transport is still very rare, To this end, based on the first principles calculation of Guo, we explored the thermal transport properties of the 2 to 10 layer silicon structure in [108].

II. COMPUTATIONAL DETAILS

Density functional theory(DFT) calculations are carried out by using the Vienna ab initio Simulation Package(VASP)16. The exchange and correlation interactions between electrons are described by the Perdew, Burke, and Ernzerhof functional(PBE)17. The projector augmented wave(PAW)18 pseudopotential is adopted to model the interaction between electrons and ions. The energy cutoff is chosen to be 520 eV for the expansion of the wave function by plane-wave basis sets. The structure of bulk is fully Relaxed with a k-point mesh of 4×4×4.

Thermal conductivity the system is calculated by using Boltzmann Transportation Equation with relaxation time approximation as implemented in ShengBTE19, in which thermal conductivity tensor is given by

(1)

The calculations of , , and require second- and third-order force constants (FCs) as inputs. Both second- and third-order FCs are extracted from density functional theory computations by using the finite displacement method. The FCs are calculated with 4×2×2 supercell with a 3×3×3 Monkhorst-Pack k-point mesh. The phonon dispersion and states density are calculated with Phonopy20 with second order force constants. The interaction range of third-order FCs is truncated up to 4th neighbor.

The thermoelectric properties including Seebeck coefficients and electric thermal conductivity are calculated with Boltzmann transportation equation(BTE) realized in Boltztrap21 with eigenvectors extracted from VASP with k-point mesh of 14x14x14.

III.RESULTS AND DISCCUSION

Bulk is consist of weakly bounded 1D strips. As shown in **FIG.1**, the optimized configuration of the Bulk possesses C2/m symmetry (space group no. 12) with an monoclinic lattice. The obtained lattice constants along the three lattice vectors are 4.445 ,8.122,11.057, and the volume of unit cell is 370.33 which are in reasonable agreement with the experiment15.

To confirm the dynamical stability of bulk , phonon dispersion is calculated in the framework of the frozen phonon method22. The along the high symmetrical path of the Brillouin zone and phonon states density are plotted in **FIG.2**. No appreciable imaginary modes are found in the first Brillouin zone, suggesting that the bulk is dynamically stable.

To further study its thermal stability at finite-temperature, we performed ab initio molecular dynamics (MD) simulations at typical temperatures and the results of Mean Square Displacement(MSD)23 are shown in **FIG.3**. The MSD is defined as

, (2)

where means the average of all the atoms.

For solids the MSD does not change while for liquids and gas it changes linearly with time. Therefore, the bulk is thermally stable in a wide temperature range from 300 K to 800 K. However, the structure starts melting when heated to 900 K. Thus we only concentrated on the trusted temperature range (300–700 K), and choose 300 K as a typical temperature to perform the thermal conductivity calculations.

To obtain reliable results of thermal conductivity, the convergence dependence to q points density has to be tested. **FIG.4**a shows the convergence of thermal conductivity on q points with N increase from 2 to 8. The TC shows its convergence at N=4, above witch the result changes a little but not the computational effort, so we choose the number of transverse q points to be both 4. Besides, the convergence on q points with N increase from 16 to 1024 is also tested as in **FIG.4**b. The result of could be a good estimate of the converged result and we choose it to calculate TC only for the trends of TC on other properties like temperature et. al to save computer resources. **FIG.4**c shows the convergence on phonon cut off free path. The exact convergence could not be obtained even at due to the abnormally large lifetime of long wave phonons show in **FIG.4**d, which always exist in low dimensional materials. However, a lot of research shows the relation of TC and phonon cut off free path obeys the rules of 24

, (3)

and **FIG.4**e verifies that it also make sense in bulk and the calculated results are over estimated. As the conclusion, the calculated results of thermal conductivity are not converged even in extremely dense q points, however they can be used as upper limited estimates of the exact results.

The thermal conductivity of is extremely low and anisotropic as shown in **FIG.5**. The TC values decreases with increasing temperature and obeys the rule of , and the largest value at 300K is much less than . The TC along the stripes are almost 3 times that of the transverse value which may result from the nature the quasi-1D structure.

Mode localization of phonons is believed to account for low thermal conductivity in this quasi-1D bulk system. To understand the underlying physical mechanism of localization of phonons on thermal conductivity, we have carried out a vibrational eigen-mode analysis. Mode localization can be quantitatively characterized by, the participation ratio25 for each eigen-mode

, (4)

where N is the total number of atoms and is the complex amplitude of atom s for eigen-mode. The participation ratio presents the fraction of atoms participating in a given mode and effectively indicates the localized modes with and delocalized modes with O (1). It can provide a more detailed information about the localization effect to each mode. The eigenvectors and frequencies are obtained using Phonopy20 with and mesh sampling. **FIG.8** shows the participation ratio of . A lot of phonons have participation ratio below 0.5 which means they are strongly localized and lost the capability to carry energy and they have little contribution to thermal conductivity.

C12N

CN

Large anharmonic would be another key factor that account for the low thermal conductivity. **FIG.6** shows the group velocity of the phonons. Although the frequencies are pretty low (phonons are pretty soft), the group velocities are not so small witch can be understood by the steep phonon dispersion, for example, along the path ΓM. The maximum group velocity is comparable to that of graphene witch possesses the largest thermal conductivity so far. So group velocity is not responsible for the low TC. The large Gruneisen parameters26 showed in **FIG.9**b means pretty large anharmonic effects in which suggest strongly three-phonon scattering effects27. **FIG.7**a shows the three-phonon scattering relaxation time of all the phonons. The mean free path are also show in **FIG.7**b.Except for the long wave ones, all the life time are pretty small and this is exactly the origin of the low TC. The scattering strength show in **FIG.9**a also shows large scattering of phonons.

Low TC means the potential of applications in thermoelectric field and is predicted to be a good thermoelectric material. **FIG.10**a shows Seebeck coefficient at different temperatures. The typical values are in the range of several mV/K and are comparable with that of SnSe. Seebeck coefficient are sensitive to temperature while **FIG.10**b shows that electric conduction are not. The power factor are shown in **FIG.10**c. Although Seebeck coefficient is smaller at 700K, power factor is higher because of the rise and fall of around fermi level. However is also higher at 700K which eliminate the difference. The electric thermal conductivity is comparable at all the temperature and is even higher, which dominant at high temperature as shown in **FIG.11**a. At this point all the factors of figure ZT of merit are collected and the final results are shown in **FIG.11**b. After some n-doping or p-doping, ZT reaches its maximum and the best values could be obtained at high temperature. At 700K this ZT value is around 0.8 and this is not bad for the application of thermoelectric energy translation.

IV. CONCLUSIONS

To summarize, in this work, we propose to study the thermal transportation properties of quasi-1D bulk material from first principle. Our numerical results demonstrate that possess thermal conductivity as low as 0.5 W/mK and its TC are strongly anisotropic and the direction along the 1D blocks is the most thermal conductive. The low thermal conductivity origins from the phonon mode localization caused by the week interaction between the 1D blocks and also origins from large anharmonic effect which accounts for the large three-phonon scatter rate. The potential of in thermoelectric application is also inspected and we found although the Seebeck coefficient is large, the low electric conductance limits the figure of merit ZT to be around 0.8 which is comparable to the current thermoelectric material 28 but not stand for the best catalog in this field. Our research shows that quasi-1D bulk materials have low thermal conductivity with large probability and is a guidance for searching of new thermoelectric materials in the future.

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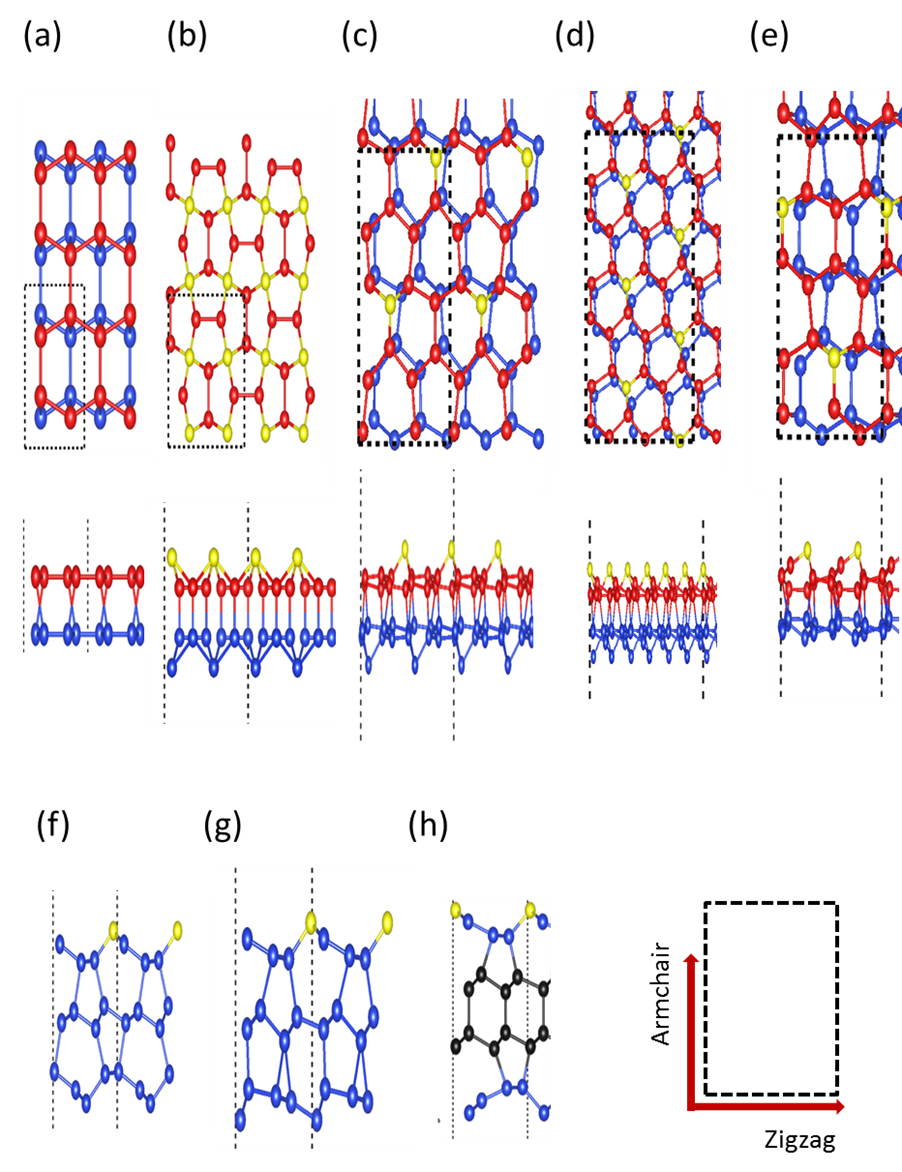
**TABLE.1.** Symmetry of the structures, binding energy Ec(eV/Si) and structure features

|  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- |
| Name | Minimal  period | Symmetry | Ec in Guo | Ec in MD | Buckling Feature |
| 2l1 | 1×1 | Cmme | 5.000 | 4.145 | Smooth |
| 2l2 | √2×√2 | C12/m1 | 4.991 | 4.204 | Large buckling and symmetric |
| 2l3 | 2×2 | C12/m1 | 5.063 | 4.257 | Large buckling and tilt symmetric |
| 2lh | 2×2 | P1 | 5.073 | 4.216 | Large buckling |
| 2lr3 | √3×√3 | P1 | - | 4.225 | Small buckling and symmetric |
| 3l1 | 2×1 | P121/m1 | 5.138 | 4.337 | - |
| 3l2 | 2×1 | P1 | 5.135 | 4.298 | - |
| 4l1 | 2×1 | P1 | 5.225 | 4.368 | - |

**TABLE.2.** The thermal conductivity and anisotropic ratio of different multi-layer silicene.



**FIG.1.** (color online) Some typical structure of multilayer silicon. Within which (a) to (e) are top view and side view of bilayer structures. (f) to (g) are side view of trilayer structures and (h) is that of four-layers. The buckling atoms on the top surface are labeled as yellow while the read atoms represent the others on the top surface. All the atoms on the bottom surface are labeled as blue. The blacks represent those that are inside the structure. The top view of the cells is shown in the last.



3l1

2l22

2l3

2lr3

2lh

3l2

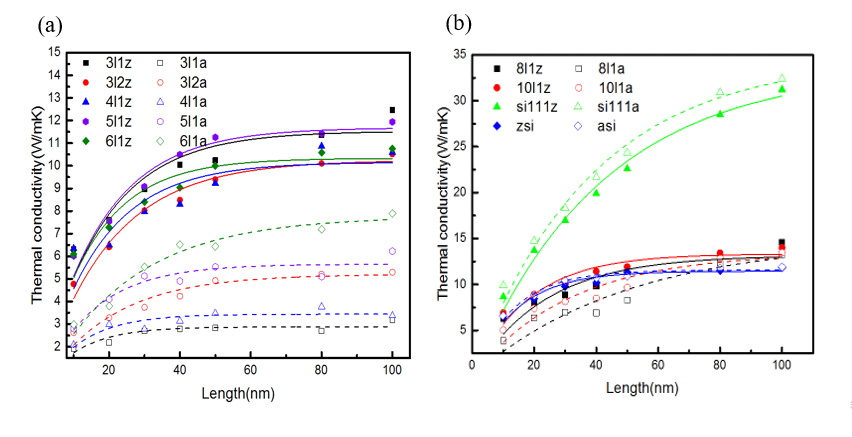
4l1

2l1

**FIG.2.** (color online) The thermal conductivity dependence on length for five types of bilayer silicon. The scatters are the results of MD simulations while the lines are fitted with Eq.1. The letter z/a in the legend mean the transport direction is zigzag/armchair.



**FIG.3.** (color online) The dependence on length of thermal conductivity for silicon with variable layers.



**FIG.4.** (color online) The phonon dispersion of multilayer silicon along high-symmetry points. (a)2l1 and (b) 2l2 are bilayer structure (c) 3l1 is trilayer structure,(d) 4l1 is four-layer structure and (e) 6l1 width six layers,(f)10l1 with ten layers.

